IN THE CLAIMS:

1. (Canceled)

2. (Previously Amended) The method as claimed in claim 8,

wherein

the auxiliary layer has a layer thickness in the range of 20 to 100 nm.

3. (Previously Amended) The method as claimed in claim 8,

wherein

the auxiliary layer is used at least partly as a hard mask for the patterning and preceding the etching by dry etching.

4. (Previously Amended) The method as claimed in claim 8,

wherein

the auxiliary layer is detected by an etching stop detection signal during the CMP process.

5. (Previously Amended) The method as claimed in claim 8,

wherein

an additional wet-chemical cleaning step is carried out at the end of the etching.

6. (Previously Amended) The method as claimed in claim 8,

wherein

the auxiliary layer is composed of diamond-like carbon, carbon polymers or of porous material.

7. (Previously Amended) The CMP process as claimed in claim 6,

wherein

the auxiliary layer is used in conjunction with a CARL resist as bottom resist.

8. (Currently Amended) A method for producing a metal contact in a dielectric comprising the steps of:

forming a contact via in said dielectric;

providing a liner made of titanium or a titanium compound on the whole area of said dielectric and in said contact via;

providing a metalization on said whole area, on said dielectric and in said contact via, wherein at least in the surroundings of said contact via, providing an auxiliary layer is ~~provided~~ on said dielectric between said dielectric and said liner, perforating said liner and said auxiliary layer ~~being removable by a Chemical Mechanical Polishing process~~; and

removing said metalization on said liner and said auxiliary layer by ~~said~~ Chemical Mechanical Polishing process, said process stopping on said dielectric, whereby upon a ~~breakthrough~~perforation of said liner and said auxiliary layer an under etch of said liner by removal of said auxiliary layer is effected such that the liner lying thereon is lifted off.